# **Switching Transistor**

# **PNP Silicon**

### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

| Rating                         | Symbol           | Value | Unit |
|--------------------------------|------------------|-------|------|
| Collector – Emitter Voltage    | V <sub>CEO</sub> | -40   | Vdc  |
| Collector – Base Voltage       | V <sub>CBO</sub> | -40   | Vdc  |
| Emitter – Base Voltage         | V <sub>EBO</sub> | -5.0  | Vdc  |
| Collector Current – Continuous | Ι <sub>C</sub>   | -600  | mAdc |
| Collector Current – Peak       | I <sub>CM</sub>  | -900  | mAdc |

#### THERMAL CHARACTERISTICS

| Characteristic  | Symbol                            | Max         | Unit        |
|---|-----------------------------------|-------------|-------------|
| Total Device Dissipation FR-5 Board<br>(Note 1) @T <sub>A</sub> = 25°C<br>Derate above 25°C         | P <sub>D</sub>                    | 225<br>1.8  | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient   | $R_{\theta JA}$                   | 556         | °C/W        |
| Total Device Dissipation Alumina<br>Substrate, (Note 2) @T <sub>A</sub> = 25°C<br>Derate above 25°C | P <sub>D</sub>                    | 300<br>2.4  | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient   | $R_{\theta JA}$                   | 417         | °C/W        |
| Junction and Storage Temperature  | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C          |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

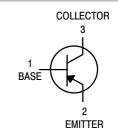
\*Transient pulses must not cause the junction temperature to be exceeded. 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



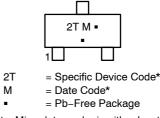
# **ON Semiconductor®**

http://onsemi.com





MARKING DIAGRAM



(Note: Microdot may be in either location)

\*Specific Device Code, Date Code or overbar orientation and/or location may vary depending upon manufacturing location. This is a representation only and actual devices may not match this drawing exactly.

#### **ORDERING INFORMATION**

| Device        | Package             | Shipping <sup>†</sup>   |
|---------------|---------------------|-------------------------|
| MMBT4403LT1G  | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel      |
| SMMBT4403LT1G | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel      |
| MMBT4403LT3G  | SOT-23<br>(Pb-Free) | 10,000 / Tape &<br>Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

| C  | Symbol  | Min                  | Мах                          | Unit                    |       |
|--|---|----------------------|------------------------------|-------------------------|-------|
| OFF CHARACTERISTICS  |   |                      | •                            |                         |       |
| Collector - Emitter Breakdown Voltage  | (Note 3) $(I_{\rm C} = -1.0 \text{ mAdc}, I_{\rm B} = 0)$                             | V <sub>(BR)CEO</sub> | -40                          | -                       | Vdc   |
| Collector – Base Breakdown Voltage   | $(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$  | V <sub>(BR)CBO</sub> | -40                          | -                       | Vdc   |
| Emitter – Base Breakdown Voltage   | $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$  | V <sub>(BR)EBO</sub> | -5.0                         | -                       | Vdc   |
| Base Cutoff Current  | $(V_{CE} = -35 \text{ Vdc}, V_{EB} = -0.4 \text{ Vdc})$                               | I <sub>BEV</sub>     | -                            | -0.1                    | μAdc  |
| Collector Cutoff Current   | (V <sub>CE</sub> = $-35$ Vdc, V <sub>EB</sub> = $-0.4$ Vdc)                           | ICEX                 | -                            | -0.1                    | μAdc  |
| ON CHARACTERISTICS   |   | ·                    |                              |                         |       |
| DC Current Gain<br>(Note 3)<br>(Note 3)  |   | h <sub>FE</sub>      | 30<br>60<br>100<br>100<br>20 | _<br>_<br>_<br>300<br>_ | _     |
| Collector - Emitter Saturation Voltage   | V <sub>CE(sat)</sub>  |                      | -0.4<br>-0.75                | Vdc                     |       |
| Base – Emitter Saturation Voltage (Not   | V <sub>BE(sat)</sub>  | -0.75                | -0.95<br>-1.3                | Vdc                     |       |
| SMALL-SIGNAL CHARACTERISTIC  | S   | ·                    | -                            |                         |       |
| Current-Gain - Bandwidth Product   | (I <sub>C</sub> = -20 mAdc, $V_{CE}$ = -10 Vdc, f = 100 MHz)                          | f <sub>T</sub>       | 200                          | -                       | MHz   |
| Collector-Base Capacitance   | Collector-Base Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$ |                      | -                            | 8.5                     | pF    |
| Emitter–Base Capacitance $(V_{BE} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$                     |   | C <sub>eb</sub>      | -                            | 30                      | pF    |
| Input Impedance $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$             |   | h <sub>ie</sub>      | 1.5                          | 15                      | kΩ    |
| /oltage Feedback Ratio $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$      |   | h <sub>re</sub>      | 0.1                          | 8.0                     | X 10- |
| Small – Signal Current Gain $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$ |   | h <sub>fe</sub>      | 60                           | 500                     | -     |
| Output Admittance  | $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$          |                      | 1.0                          | 100                     | μMhos |
| SWITCHING CHARACTERISTICS  |   |                      |                              |                         |       |
| Delay Time   | (V <sub>CC</sub> = -30 Vdc, V <sub>EB</sub> = -2.0 Vdc,                               | t <sub>d</sub>       | -                            | 15                      | 200   |
| Rise Time  | $I_{\rm C} = -150 \text{ mAdc}, I_{\rm B1} = -15 \text{ mAdc})$                       | t <sub>r</sub>       |                              | 20                      | ns    |
| Storage Time   | $(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc},$                                 | t <sub>s</sub>       | -                            | 225                     | ns    |
| Fall Time  | I <sub>B1</sub> = I <sub>B2</sub> = -15 mAdc)   |                      | -                            | 30                      | 113   |

3. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

## SWITCHING TIME EQUIVALENT TEST CIRCUIT

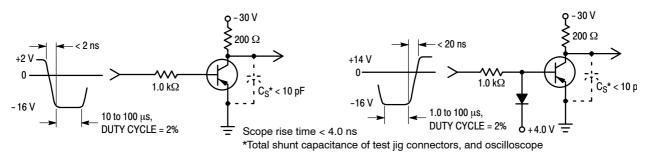
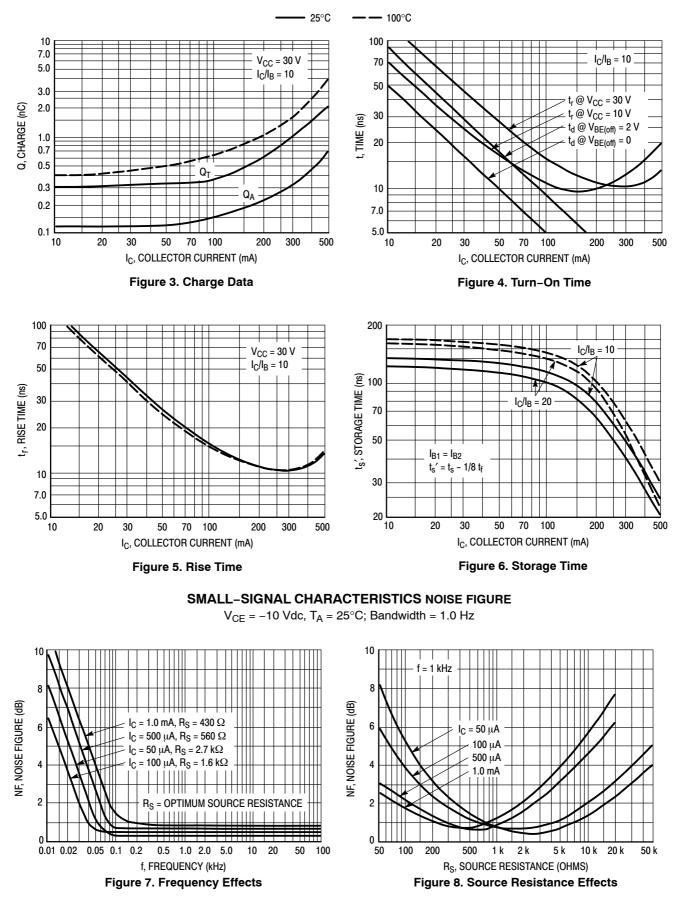


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

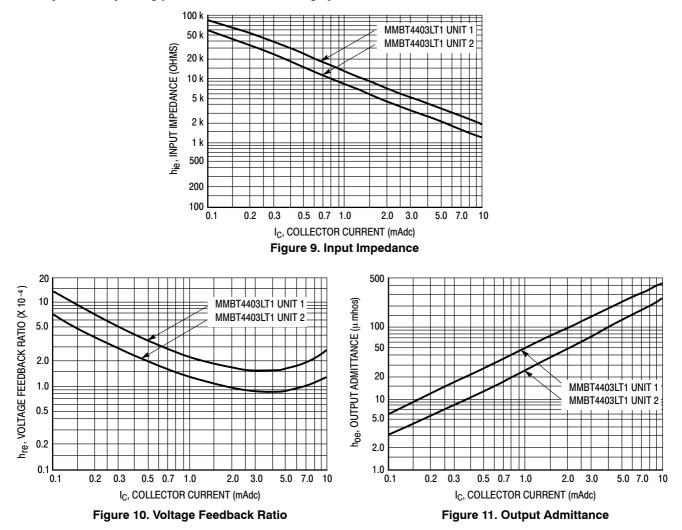
#### **TRANSIENT CHARACTERISTICS**



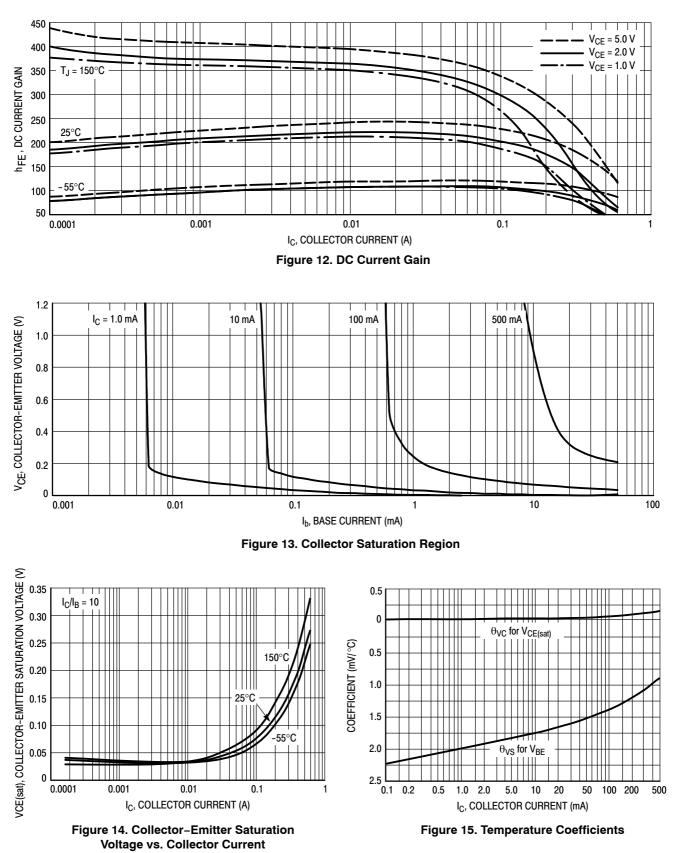
## h PARAMETERS

# $V_{CE}$ = 10 Vdc, f = 1.0 kHz, T<sub>A</sub> = 25°C

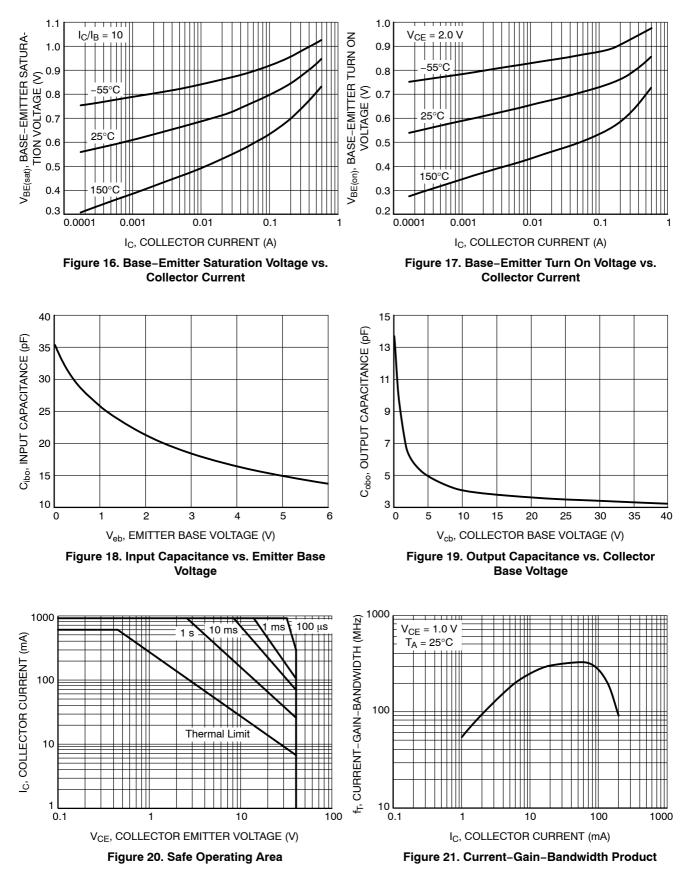
This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high–gain and a low–gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.



**STATIC CHARACTERISTICS** 

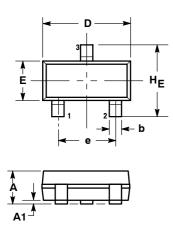


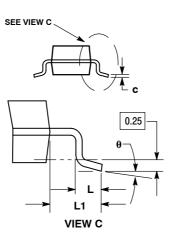
## STATIC CHARACTERISTICS



#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP** 





NOTES

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2.

1992. 2. CONTROLLING DIMENSION: INCH. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM 3

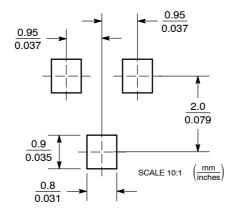
THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. 4

| PROT | RUSIONS OB GATE BURRS. |      |      | INCHES |       |       |
|------|------------------------|------|------|--------|-------|-------|
| DIM  | MIN                    | NOM  | MAX  | MIN    | NOM   | MAX   |
| Α    | 0.89                   | 1.00 | 1.11 | 0.035  | 0.040 | 0.044 |
| A1   | 0.01                   | 0.06 | 0.10 | 0.001  | 0.002 | 0.004 |
| b    | 0.37                   | 0.44 | 0.50 | 0.015  | 0.018 | 0.020 |
| с    | 0.09                   | 0.13 | 0.18 | 0.003  | 0.005 | 0.007 |
| D    | 2.80                   | 2.90 | 3.04 | 0.110  | 0.114 | 0.120 |
| Е    | 1.20                   | 1.30 | 1.40 | 0.047  | 0.051 | 0.055 |
| е    | 1.78                   | 1.90 | 2.04 | 0.070  | 0.075 | 0.081 |
| L    | 0.10                   | 0.20 | 0.30 | 0.004  | 0.008 | 0.012 |
| L1   | 0.35                   | 0.54 | 0.69 | 0.014  | 0.021 | 0.029 |
| ΗE   | 2.10                   | 2.40 | 2.64 | 0.083  | 0.094 | 0.104 |
| θ    | 0°                     |      | 10°  | 0°     |       | 10°   |

STYLE 6: PIN 1. BASE EMITTER 2 З.

COLLECTOR

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All or operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: MMBT4403LT1G MMBT4403LT3G SMMBT4403LT1G